

New Product

N-Channel 30-V (D-S) 175°C MOSFET

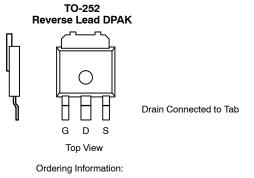
PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}$ (Ω)	I _D (A) ^b		
30	0.0065 @ V _{GS} = 10 V	84 ^b		
	0.0095 @ V _{GS} = 4.5 V	59 ^b		

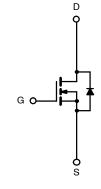
FEATURES

- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- Optimized for Low-Side Synchronous Rectifier Operation
- 100% R_g Tested

APPLICATIONS

- DC/DC Converters
 - Desktop CPU Core
- Synchronous Rectifiers





Ordering Information:
SUR50N03-06P—E3
SUR50N03-06P-T4—E3 (altrenate tape orientation)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (TA = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	,,	
Gate-Source Voltage		V _{GS}	±20		
	T _A = 25°C		27		
Continuous Drain Current	T _C = 25°C	I _D	84 ^b		
	T _C = 100°C		59 ^b	A	
Pulsed Drain Current		I _{DM}	100		
Continuous Source Current (Diode Conduction) ^a		I _S	25		
	T _C = 25°C	_	88		
Maximum Power Dissipation	T _A = 25°C	P _D	8.3 ^a	w	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 10 sec	R _{thJA}	15	18	°C/W
Maximum Junction-to-Ambient ^a	Steady State		40	50	
Maximum Junction-to-Case		R _{thJC}	1.4	1.7	

Notes

- a. Surface Mounted on FR4 Board, $t \le 10$ sec.
- b. Based on maximum allowable junction temperature, package limitation current is 50 A.

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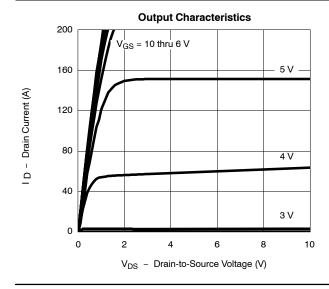
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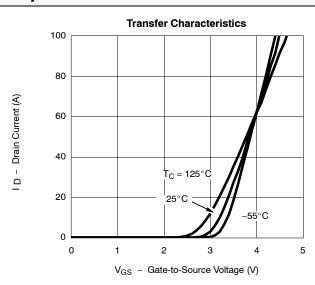


SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit	
Static	•		•	1			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	30			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0		3.0		
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			±100	nA	
7 0 1 1/1 10 1 0 1		V _{DS} = 30 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	DSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125^{\circ}\text{C}$			50	μΑ	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			Α	
		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.0053	0.0065		
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 125°C			0.0105	Ω	
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0078	0.0095		
Forward Transconductance ^b	9fs	V _{DS} = 15 V, I _D = 20 A	20			S	
Dynamic ^a							
Input Capacitance	C _{iss}			3100		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		565			
Reverse Transfer Capacitance	C _{rss}			255			
Gate Resistance	R _g		1	1.9	3.1	Ω	
Total Gate Charge ^c	Qg			21	30	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 15 \text{ V}, \ V_{GS} = 4.5 \text{ V}, \ I_D = 50 \text{ A}$		10			
Gate-Drain Charge ^c	Q_{gd}			7.5			
Turn-On Delay Time ^c	t _{d(on)}			12	20		
Rise Time ^c	t _r	V_{DD} = 15 V, R_L = 0.3 Ω		12	20	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		30	45		
Fall Time ^c	t _f			10	15		
Source-Drain Diode Ratings and	d Characteristi	c (T _C = 25°C)					
Pulsed Current	I _{SM}				100	Α	
Diode Forward Voltageb	V _{SD}	I _F = 100 A, V _{GS} = 0 V		1.2	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 50 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		35	70	ns	

- Guaranteed by design, not subject to production testing. Pulse test; pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





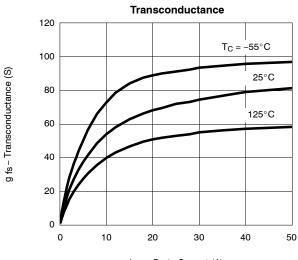




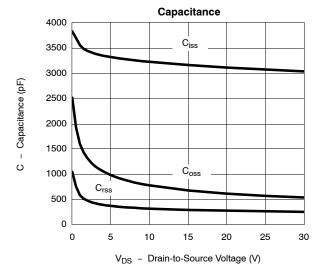


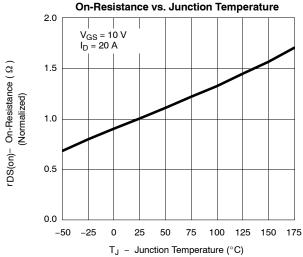
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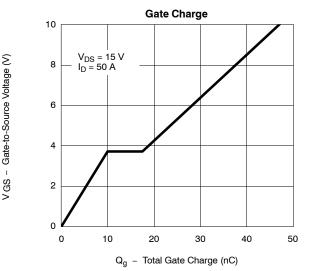


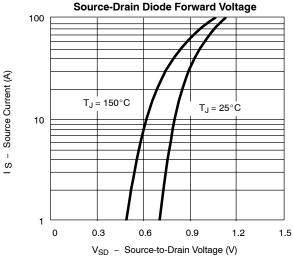




On-Resistance vs. Drain Current 0.0150 0.0125 rDS(on)- On-Resistance (Ω) 0.0100 V_{GS} = 4.5 V 0.0075 $V_{GS} = 10 \text{ V}$ 0.0050 0.0025 0.0000 0 20 40 60 80 100

I_D - Drain Current (A)



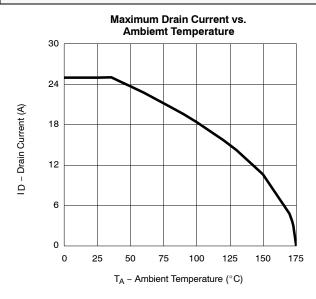


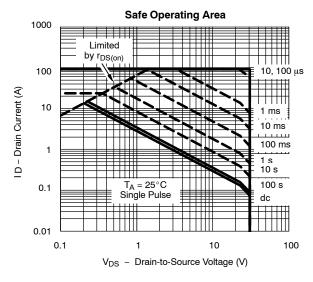
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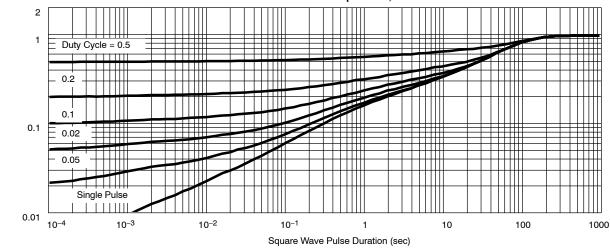


THERMAL RATINGS

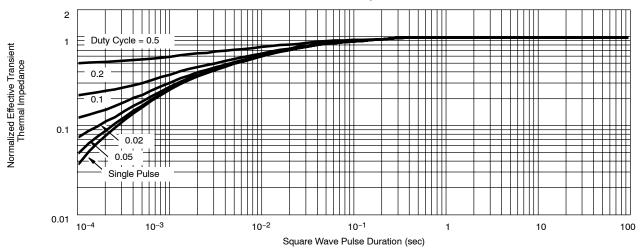




Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



Normalized Effective Transient Thermal Impedance

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